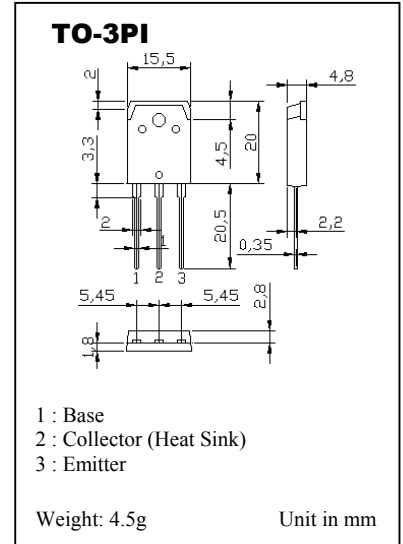


NPN SILICON TRIPLE DIFFUSED PLANAR TRANSISTOR

...designed for 140V/12A AF 60W output application.
 ...complementary to PMB817.

MAXIMUM RATINGS (Ta= 25 °C)

Characteristic	Symbol	Value	Unit
Collector Base Voltage	VCBO	160	V
Collector Emitter Voltage	VCEO	140	V
Emitter Base Voltage	VEBO	6	V
Collector Current	IC	12	A
Collector Current (Pulse)	ICP	15	A
Collector Power Dissipation Tc = 25 °C	Pc	100	W
Junction Temperature	Tj	150	°C
Storage Temperature Range	Tstg	-40 ~ 150	°C



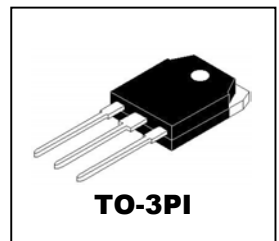
ELECTRICAL CHARACTERISTICS (Ta= 25 °C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector Cutoff Current	ICBO	VCB = 80V, IE = 0	-	-	0.1	mA
Emitter Cutoff Current	IEBO	VEB = 4V, IC = 0	-	-	0.1	mA
DC Current Gain	hFE(1)	VCE = 5V, IC = 1A	60	-	200	-
	hFE(2)	VCE = 5V, IC = 6A	20	-	-	-
Transition Frequency	ft	VCE = 5V, IC = 1A	-	15	-	MHz
Output Capacitance	Cob	VCB = 10V, f = 1MHz	-	210	-	pF

**NPN SILICON
 TRIPLE DIFFUSED
 TRANSISTOR**

CLASSIFICATIONS OF hFE(1)

Rank	D	E
Range	60 to 120	100 to 200



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